TOSHIBA Transistor Silicon NPN Epitaxial Type (Darlington Power)

# 2SD2686

# Solenoid Drive Applications Motor Drive Applications

- High DC current gain:  $h_{FE} = 2000$  (min) ( $V_{CE} = 2$  A,  $I_{C} = 1$  A)
- Zener diode included between collector and base

### Maximum Ratings (Ta = 25°C)

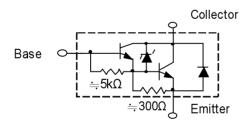
| Characteristic              |          | Symbol                | Rating     | Unit |  |
|-----------------------------|----------|-----------------------|------------|------|--|
| Collector-base voltage      |          | V <sub>CBO</sub>      | 50         | V    |  |
| Collector-emitter voltage   |          | V <sub>CEO</sub>      | 60±10      | V    |  |
| Emitter-base voltage        |          | V <sub>EBO</sub>      | 8          | ٧    |  |
| Collector current           | DC       | IC                    | 1          | Α    |  |
|                             | Pulse    | ICP                   | 3          |      |  |
| Base current                |          | lΒ                    | 0.5        | Α    |  |
| Collector power dissipation | DC       | P <sub>C</sub> (Note) | 1.0        | w    |  |
|                             | t = 10 s | LC(More)              | 2.5        |      |  |
| Junction temperature        |          | Tj                    | 150        | °C   |  |
| Storage temperature range   |          | T <sub>stg</sub>      | _55 to 150 | °C   |  |

Note: Mounted on an FR4 board (glass-epoxy; 1.6 mm thick; Cu area, 645 mm²)

# Unit: mm 4.6 MAX. 1.7 MAX 0.4 ± 0.05 1.5 ± 0.1 1.5

Weight: 0.05 g (typ.)

### **Equivalent Circuit**

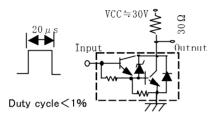


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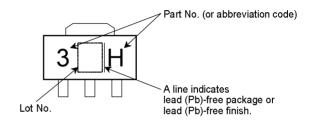
# Electrical Characteristics (Ta = 25°C)

| Characteristic                       |              | Symbol                    | Test Condition   | Min  | Тур. | Max | Unit |
|--------------------------------------|--------------|---------------------------|--|------|------|-----|------|
| Collector cutoff current             |              | ICBO                      | V <sub>CB</sub> = 45 V, I <sub>E</sub> = 0   | _    | -    | 10  | μA   |
|                                      |              | ICEO                      | V <sub>CE</sub> = 45 V, I <sub>E</sub> = 0   | _    |      | 10  | μA   |
| Emitter cutoff current               |              | I <sub>EBO</sub>          | $V_{	ext{EB}} = 8 \text{ V, } I_{	ext{C}} = 0$   | 0.80 | 1    | 4.0 | mA   |
| Collector-emitter breakdown voltage  |              | V (BR) CEO                | $I_C = 10 \text{ mA}, I_B = 0$   | 50   | 60   | 70  | V    |
| DC current gain                      |              | hFE                       | $V_{CE} = 2 \text{ V, } I_{C} = 1.0 \text{ A}$   | 2000 | _    | _   |      |
| Collector-emitter saturation voltage |              | VCE (sat) (1)             | $I_C = 0.5 \text{ A}, I_B = 1 \text{ mA}$  | _    | _    | 1.2 | V    |
|                                      |              | V <sub>CE</sub> (sat) (2) | $I_C = 1.0 \text{ A}, I_B = 1 \text{ mA}$  | _    | _    | 1.5 | V    |
| Base-emitter saturation voltage      |              | V <sub>BE (sat)</sub>     | I <sub>C</sub> = 1.0 A, I <sub>B</sub> = 1 mA  | _    | _    | 2.0 | V    |
| Switching time                       | Rise time    | t <sub>on</sub>           | See Figure 1 circuit diagram.<br>$V_{CC} \simeq 30 \text{ V}, \text{ R}_1 = 30 \Omega$ | _    | 0.4  | _   | μs   |
|                                      | Storage time | t <sub>stg</sub>          |  | _    | 4.0  |     |      |
|                                      | Fall time    | tf                        | VCC ≈ 30 V, INL = 30 52  | _    | 0.6  | _   |      |

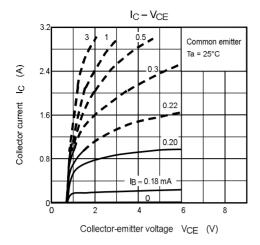
Figure 1. Switching Time Test Circuit & Timing Chart

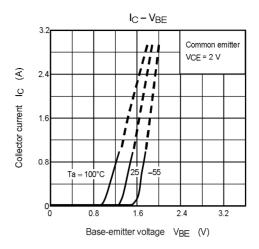


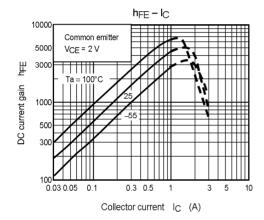
# Marking

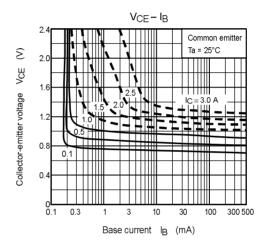


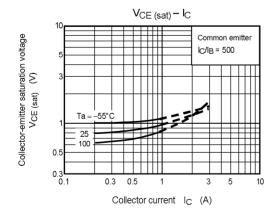
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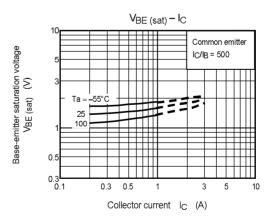


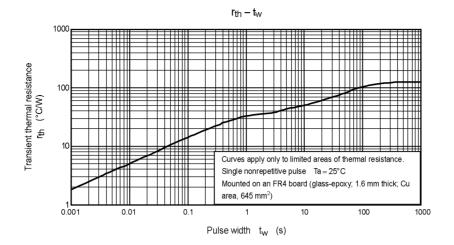


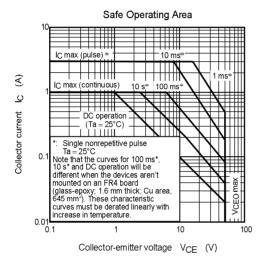












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